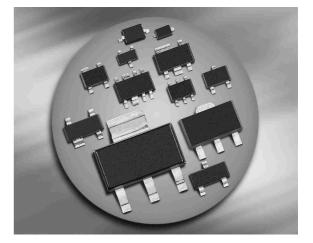


### **Silicon Tuning Diodes**

- Extended frequency range up to 2.5 GHz; spezial design for use in TV-sat tuners
- High capacitance ratio
- Pb-free (RoHS compliant) package





### BB833



| Туре  | Package | Configuration | L <sub>S</sub> (nH) | Marking |
|-------|---------|---------------|---------------------|---------|
| BB833 | SOD323  | single        | 1.8                 | white X |

## **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

| Parameter                   | Symbol           | Value   | Unit |  |
|-----------------------------|------------------|---------|------|--|
| Diode reverse voltage       | V <sub>R</sub>   | 30      |      |  |
| Peak reverse voltage-       | V <sub>RM</sub>  | 35      |      |  |
| $R \ge 5 \mathrm{k}\Omega$  |                  |         |      |  |
| Forward current             | I <sub>F</sub>   | 20      | mA   |  |
| Operating temperature range | T <sub>op</sub>  | -55 150 | °C   |  |
| Storage temperature         | T <sub>stg</sub> | -55 150 |      |  |



| Parameter   | Symbol                            | Values |      |      | Unit |
|---|-----------------------------------|--------|------|------|------|
|   |                                   | min.   | typ. | max. |      |
| DC Characteristics  |                                   |        |      |      |      |
| Reverse current   | I <sub>R</sub>                    |        |      |      | nA   |
| V <sub>R</sub> = 30 V   |                                   | -      | -    | 20   |      |
| V <sub>R</sub> = 30 V, <i>T</i> <sub>A</sub> = 85 °C          |                                   | -      | -    | 500  |      |
| AC Characteristics  |                                   |        |      |      |      |
| Diode capacitance   | CT                                |        |      |      | pF   |
| V <sub>R</sub> = 1 V, <i>f</i> = 1 MHz                        |                                   | 8.5    | 9.3  | 10   |      |
| V <sub>R</sub> = 28 V, <i>f</i> = 1 MHz                       |                                   | 0.6    | 0.75 | 0.9  |      |
| Capacitance ratio   | C <sub>T1</sub> /C <sub>T28</sub> | 11     | 12.4 | -    |      |
| V <sub>R</sub> = 1 V, V <sub>R</sub> = 28 V, <i>f</i> = 1 MHz |                                   |        |      |      |      |
| Capacitance matching <sup>1)</sup>                            | $\Delta C_{T}/C_{T}$              | -      | -    | 3    | %    |
| V <sub>R</sub> = 1 V, V <sub>R</sub> = 28 V, <i>f</i> = 1 MHz |                                   |        |      |      |      |
| Series resistance   | r <sub>S</sub>                    | -      | 1.8  | -    | Ω    |
| V <sub>R</sub> = 1 V, <i>f</i> = 470 MHz                      |                                   |        |      |      |      |

# **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

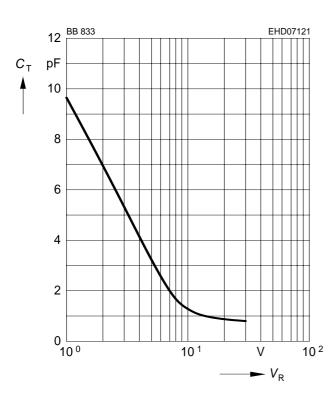
<sup>1</sup>For details please refer to Application Note 047.



BB833...

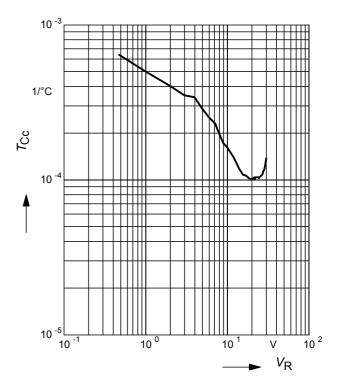
## **Diode capacitance** $C_{T} = f(V_{R})$

f = 1 MHz

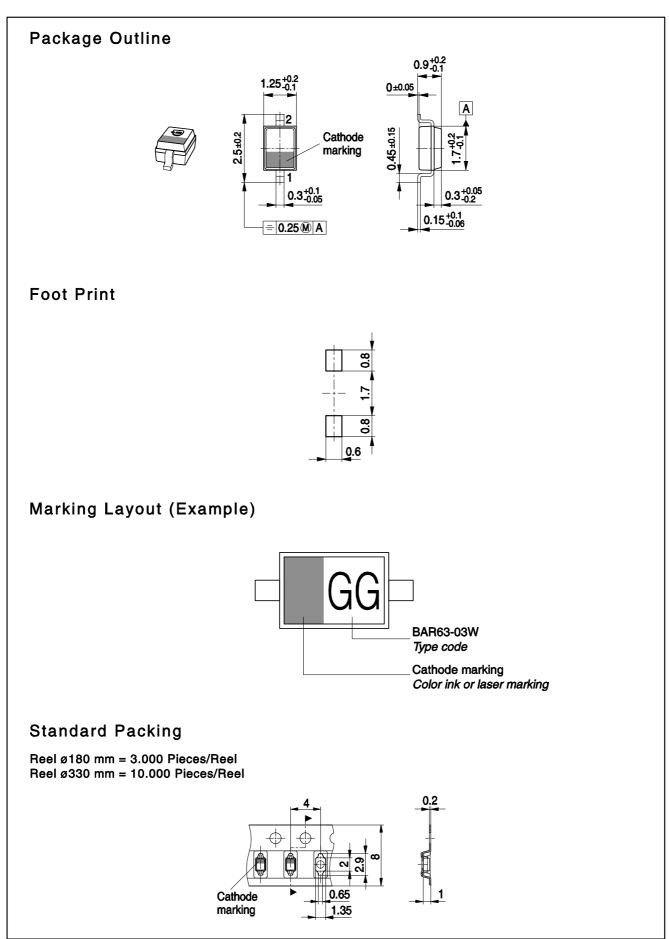


## Temperature coefficient of the diode

capacitance  $T_{Cc} = f(V_R)$ 









Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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